

Silicon P Channel MOS Type (U-MOS III)/Silicon Epitaxial Schottky Barrier Diode

SSM5G10TU

DC-DC Converter Applications

- 1.8-V drive
- Combines a P-channel MOSFET and a Schottky barrier diode in one package.
- Low $R_{DS(ON)}$ and Low V_F

Absolute Maximum Ratings

MOSFET ($T_a = 25^\circ\text{C}$)

Characteristics	Symbol	Rating	Unit
Drain-Source voltage	V_{DS}	-20	V
Gate-Source voltage	V_{GSS}	± 8	V
Drain current	DC	I_D	A
	Pulse	I_{DP} (Note 2)	
Drain power dissipation	P_D (Note 1)	0.5	W
	$t = 10\text{ s}$	0.8	
Channel temperature	T_{ch}	150	$^\circ\text{C}$

Schottky Barrier Diode ($T_a = 25^\circ\text{C}$)

Characteristics	Symbol	Rating	Unit
Repetitive peak reverse voltage	V_{RRM}	20	V
Average forward current	$I_{F(AV)}$	0.7	A
Peak one cycle surge forward current	I_{FSM}	2 (50 Hz)	A
Junction temperature	T_j	125	$^\circ\text{C}$

MOSFET and Diode ($T_a = 25^\circ\text{C}$)

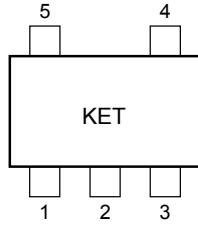
Characteristics	Symbol	Rating	Unit
Storage temperature range	T_{stg}	-55 to 125	$^\circ\text{C}$

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

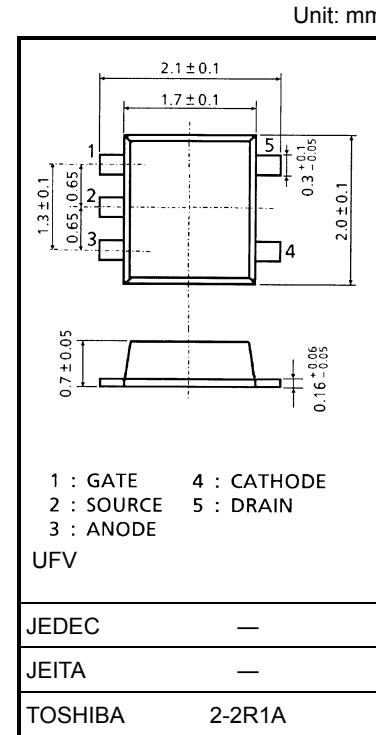
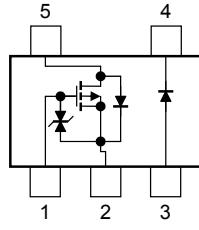
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc.).

Note 1: Mounted on FR4 board
(25.4 mm \times 25.4 mm \times 1.6 mm, Cu pad: 645 mm²)

Marking



Equivalent Circuit (top view)



Weight: 7 mg (typ.)

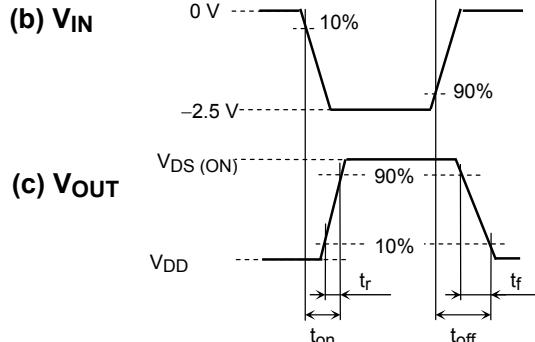
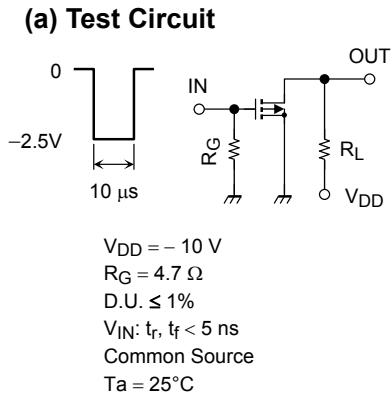
MOSFET

Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Conditions	Min	Typ.	Max	Unit
Drain-source breakdown voltage	V (BR) DSS	$I_D = -1 \text{ mA}, V_{GS} = 0 \text{ V}$	-20	—	—	V
	V (BR) DSX	$I_D = -1 \text{ mA}, V_{GS} = +8 \text{ V}$	-12	—	—	
Drain cutoff current	I_{DSS}	$V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}$	—	—	-10	μA
Gate leakage current	I_{GSS}	$V_{GS} = \pm 8 \text{ V}, V_{DS} = 0 \text{ V}$	—	—	± 1	μA
Gate threshold voltage	V_{th}	$V_{DS} = -3 \text{ V}, I_D = -1 \text{ mA}$	-0.3	—	-1.0	V
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = -3 \text{ V}, I_D = -1 \text{ A}$ (Note 2)	1.6	3.2	—	S
Drain-source ON-resistance	$R_{DS (\text{ON})}$	$I_D = -1.0 \text{ A}, V_{GS} = -4 \text{ V}$ (Note 2)	—	160	213	$\text{m}\Omega$
		$I_D = -0.8 \text{ A}, V_{GS} = -2.5 \text{ V}$ (Note 2)	—	210	294	
		$I_D = -0.1 \text{ A}, V_{GS} = -1.8 \text{ V}$ (Note 2)	—	280	430	
Input capacitance	C_{iss}	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	—	250	—	pF
Output capacitance	C_{oss}		—	43	—	
Reverse transfer capacitance	C_{rss}		—	35	—	
Total Gate Charge	Q_g	$V_{DS} = -10 \text{ V}, I_D = -1.5 \text{ A}$ $V_{GS} = -4 \text{ V}$	—	6.4	—	nC
Gate-Source Charge	Q_{gs}		—	4.5	—	
Gate-Drain Charge	Q_{gd}		—	1.9	—	
Switching time	Turn-on time	t_{on}	$V_{DD} = -10 \text{ V}, I_D = -1 \text{ A},$ $V_{GS} = 0 \text{ to } -2.5 \text{ V}, R_G = 4.7 \Omega$	—	12	ns
	Turn-off time	t_{off}		—	11.2	
Drain-source forward voltage	V_{DSF}	$I_D = 1.5 \text{ A}, V_{GS} = 0 \text{ V}$ (Note 2)	—	0.88	1.2	V

Note 2: Pulse test

Switching Time Test Circuit



Precaution

V_{th} can be expressed as voltage between gate and source when the low operating current value is $I_D = -1 \text{ mA}$ for this product. For normal switching operation, V_{GS} (on) requires a higher voltage than V_{th} and V_{GS} (off) requires a lower voltage than V_{th} .

(The relationship can be established as follows: V_{GS} (off) < V_{th} < V_{GS} (on))

Be sure to take this into consideration when using the device.

Schottky Barrier Diode**Electrical Characteristics (Ta = 25°C)**

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Peak forward voltage	V _{FM} (1)	I _F = 0.5 A	—	0.32	0.39	V
Peak forward voltage	V _{FM} (2)	I _F = 0.7 A	—	0.36	0.43	V
Repetitive peak reverse current	I _{RRM}	V _R = 6 V	—	25	150	μA
Junction capacitance	C _T	V _R = 0 V, f = 1 MHz	—	143	—	pF

Precaution

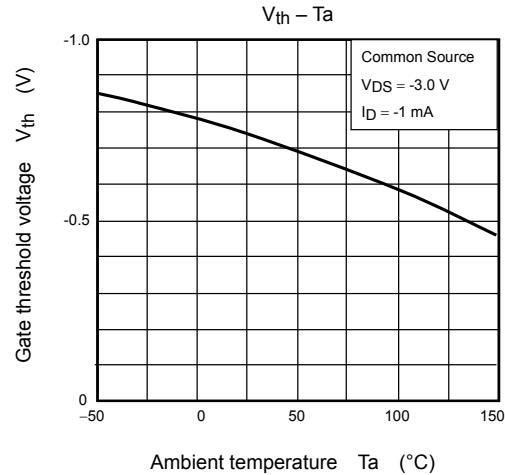
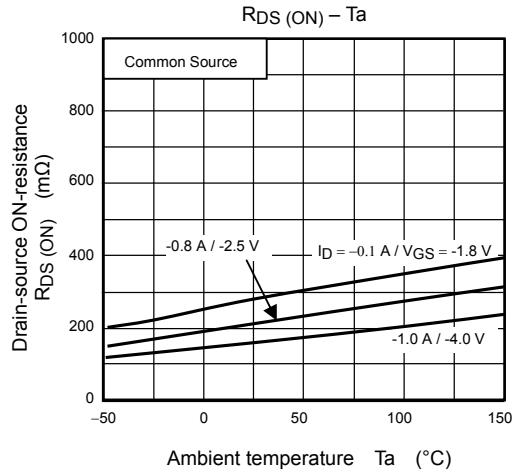
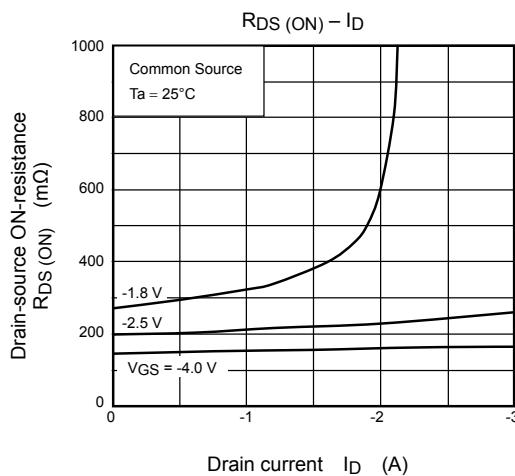
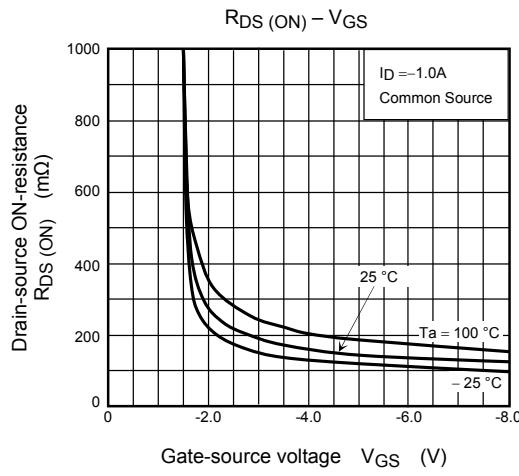
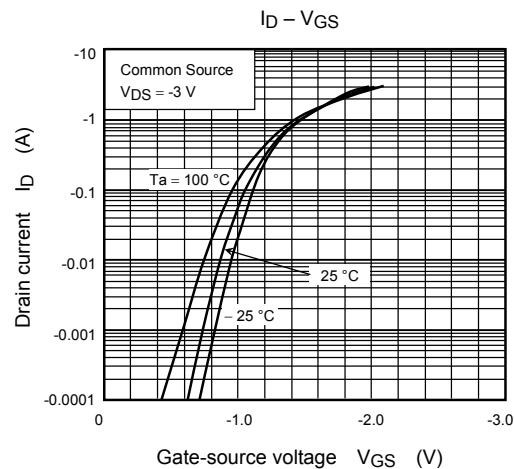
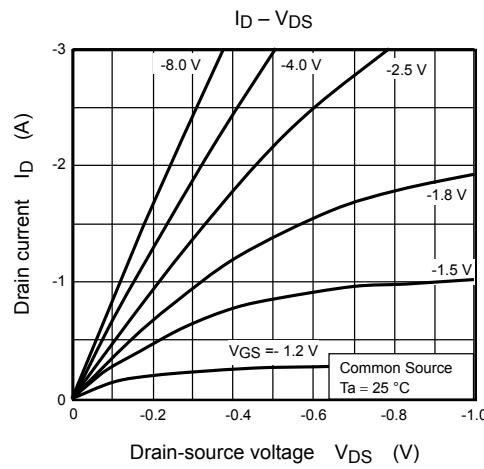
The Schottky barrier diode in this device has large reverse current leakage compared to typical switching diodes. Thus, excessive operating temperature or voltage may cause thermal runaway. To avoid this problem, be sure to take both forward and reverse loss into consideration.

Handling Precaution

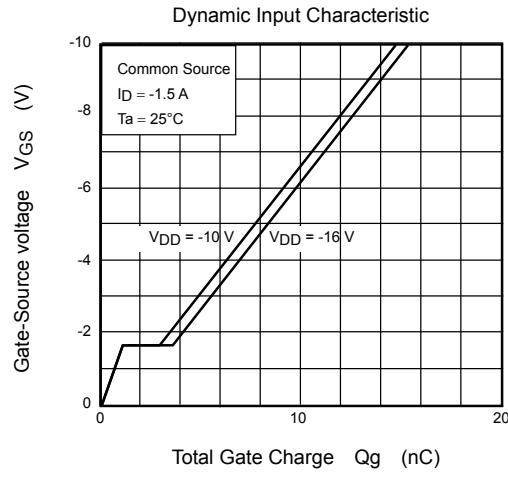
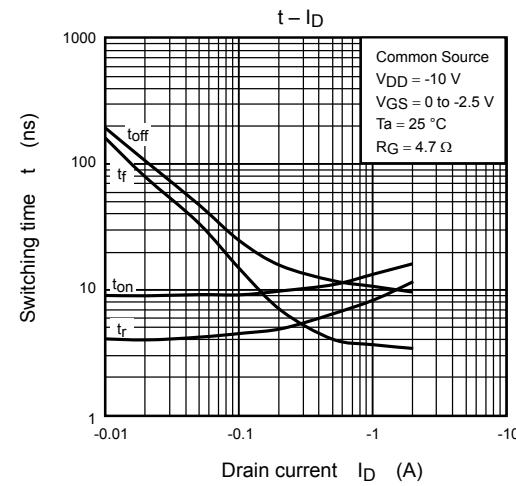
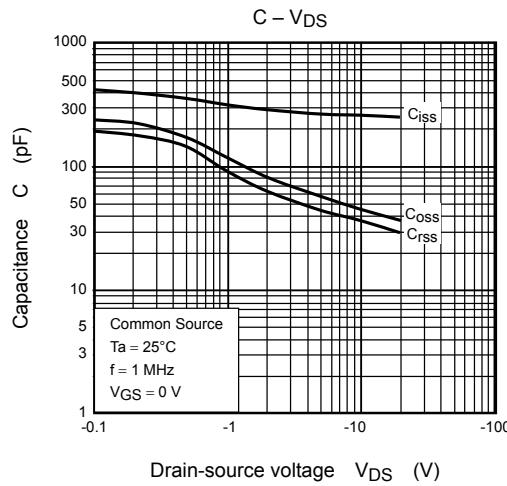
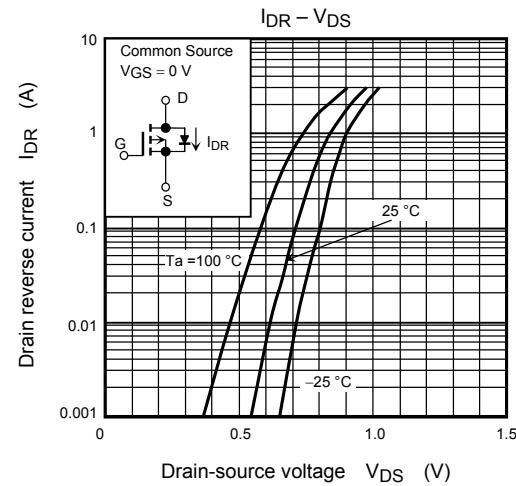
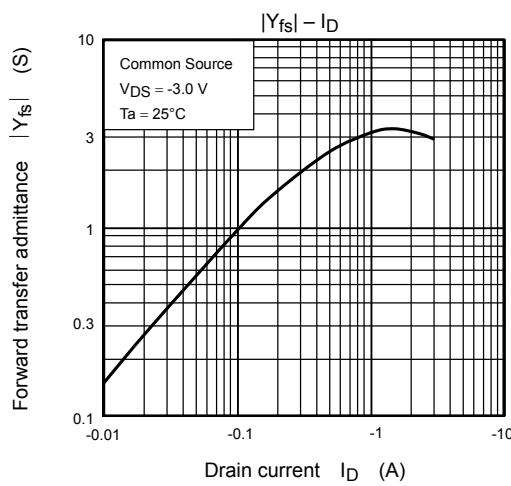
When handling individual devices that are not yet mounted on a circuit board, make sure that the environment is protected against electrostatic discharge. Operators should wear antistatic clothing, and containers and other objects that come into direct contact with devices should be made of antistatic materials.

The Channel-to-Ambient thermal resistance $R_{th\ (ch-a)}$ and the drain power dissipation P_D vary according to the board material, board area, board thickness and pad area. When using this device, be sure to take heat dissipation fully into account.

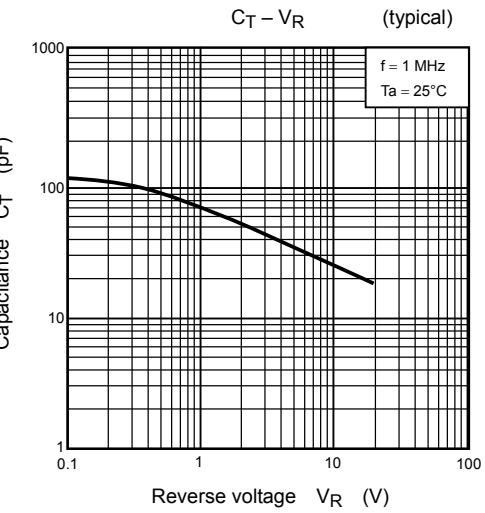
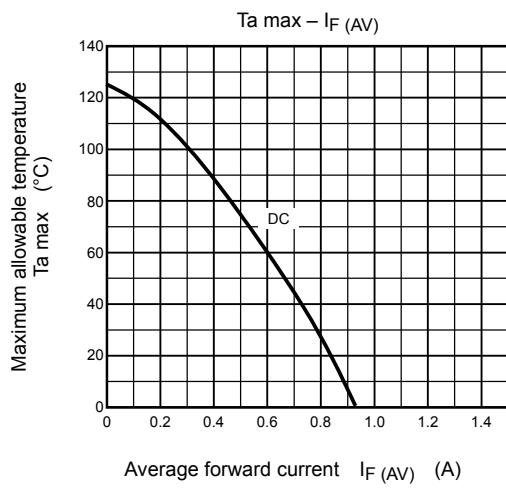
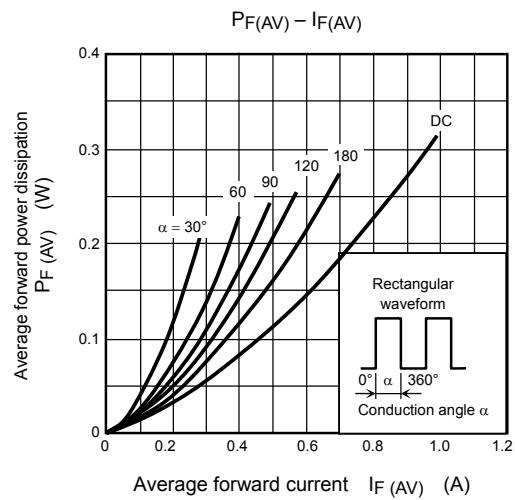
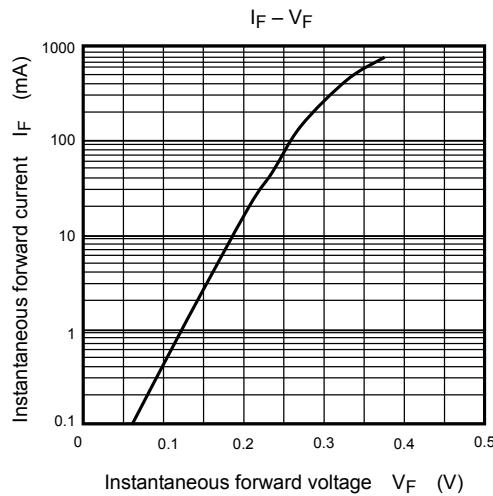
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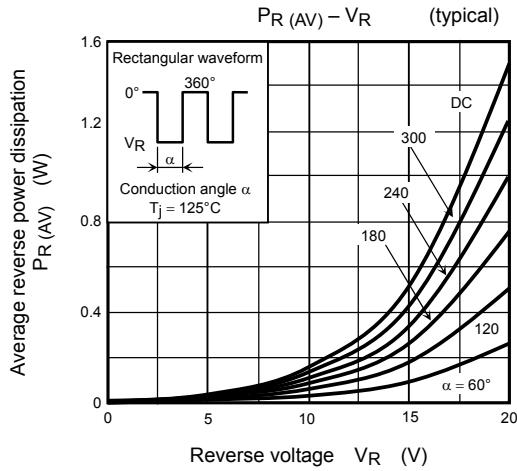
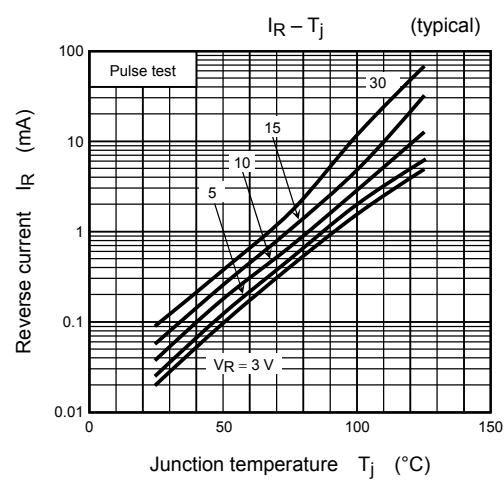
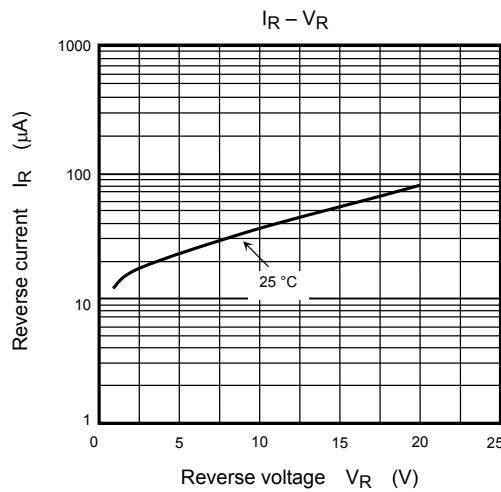
MOSFET



Schottky Barrier Diode



Schottky Diode



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20070701-EN GENERAL

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